Abstracts

High Power 6-18 GHz H/V Switch Designed in Channelized Wafer Scale Fabrication Process

N. Jain and P. Onno. "High Power 6-18 GHz H/V Switch Designed in Channelized Wafer Scale Fabrication Process." 1996 MTT-S International Microwave Symposium Digest 96.2 (1996 Vol. II [MWSYM]): 955-958.

A 6-18GHz transfer switch is fabricated by a batch process technology, the HMIC (Heterolithic Microwave Integrated Circuit) process using shunt silicon diodes. The fabrication and design utilized a novel transmission medium incorporating signal channelization for high frequency high performance operation.

❑ Return to main document.